Last Search 4/20/01

Search	L No.	Hits	Text Search	Data Bases	
			(("365-109,117,121") or ("430/365") or	USPAT; EPO; JPO;	
IS&R	1.1	871	("438-3")).CCI S.	4/20/01/21:44 Derwent; IBM TDB	
				USPAT; FPO; JPO;	
BRS	1.2	219	1 and pzt	4/20/01/21:46 Derwent; IBM TDB	
				USPAT; EPO; JPO;	
BRS	L3	53	2 and dry adj etch\$	4/20/01/21:47 Derwent; IBM TDB	

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
			Conductive diffusion barrier layer.			
	ļ		semiconductor device having the same.			
US 6177284 B1	20010123	9	and manufacturing thereof	438/3	İ	Horii, Hideki , et al.
			Stable high-dielectric-constant material	1		
US 6117689 A	20000912	16	electrode and method	438/3	438/240 ; 438/396	Summerfelt, Scott R.
					148/DIG.100;	
			Method for making LSCO stack		148/DIG.14:	
US 5614438 A	19970325	6	electrode	438/3	216/12 : 438/240	Evans, Jr., Joseph T., et al.
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